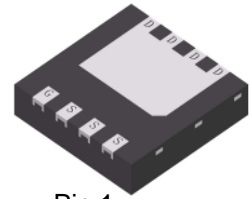


S-LPB8660DT0AG

60V P-Channel Power MOSFET



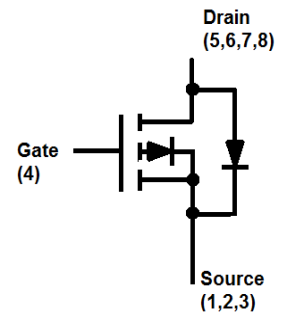
Pin 1
DFN3333-8A

1. FEATURES

- Low thermal impedance
- Fast switching speed
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. APPLICATIONS

- Load Switches
- DC/DC Conversion
- Motor Drives



3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
S-LPB8660DT0AG	P6C	2000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		VDS	-60	V
Gate-Source Voltage		VGS	±20	
Continuous Drain Current (Note1)	TA = 25°C	ID	-3.8	A
	TA = 70°C		-3.1	
	TC = 25°C		-13	
	TC = 70°C		-11	
Pulsed Drain Current (Note 2)		IDM	-15	
Avalanche Current(L=0.1mH)		IAS	15	A
Avalanche energy(L=0.1mH)		EAS	11.25	mJ
Power Dissipation (Note1)	TA = 25°C	PD	1.7	W
	TC = 25°C		20	
Operating Junction and Storage Temperature Range		TJ,Tstg	-55~+150	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance,Junction-to-Ambient(Note 1)	RθJA	71	°C/W
Thermal Resistance,Junction-to-Case	RθJC	6	

- 1.Surface mounted on "1.5 x 1.5" FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature

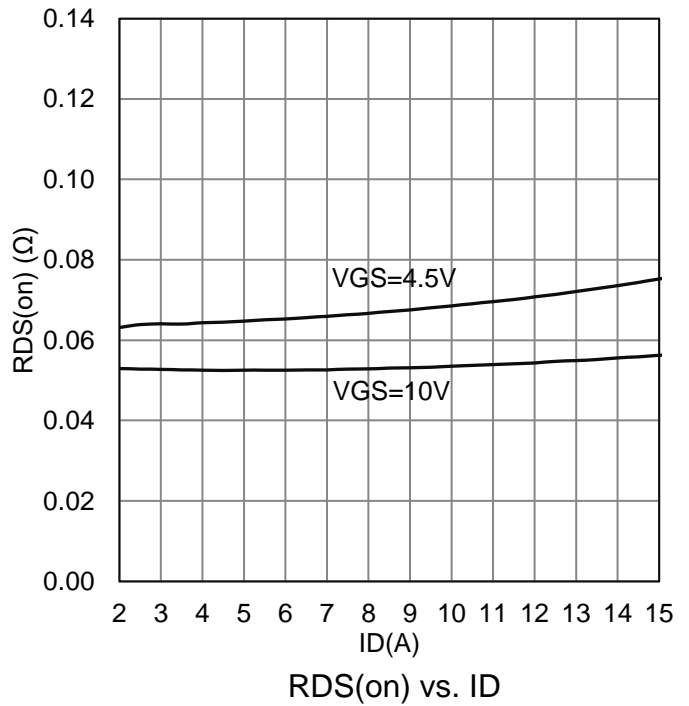
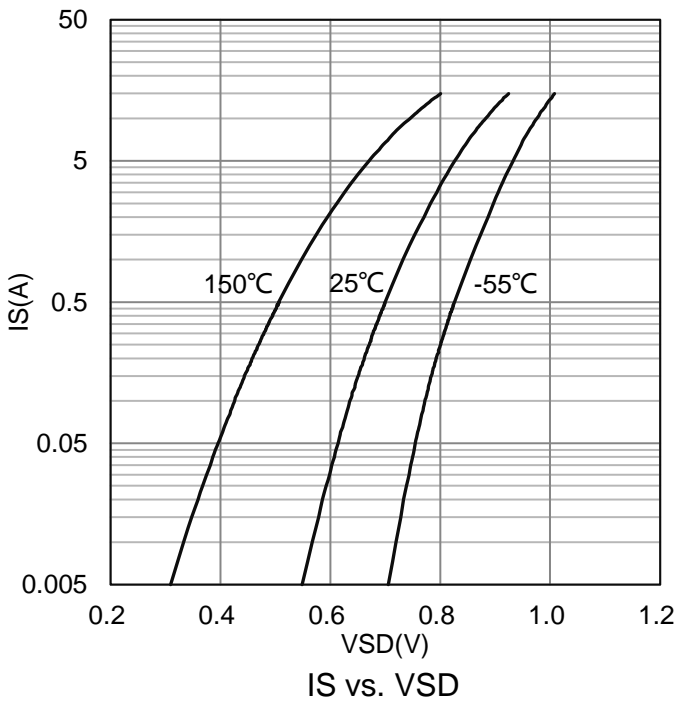
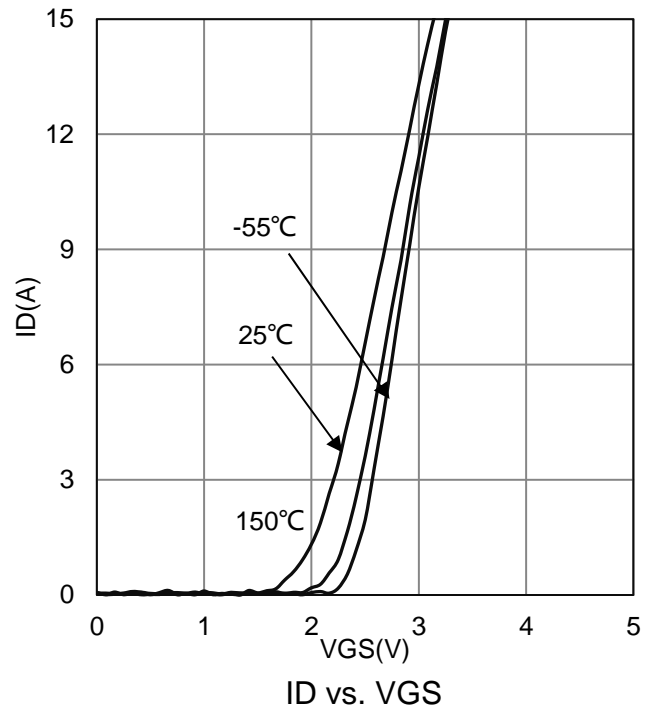
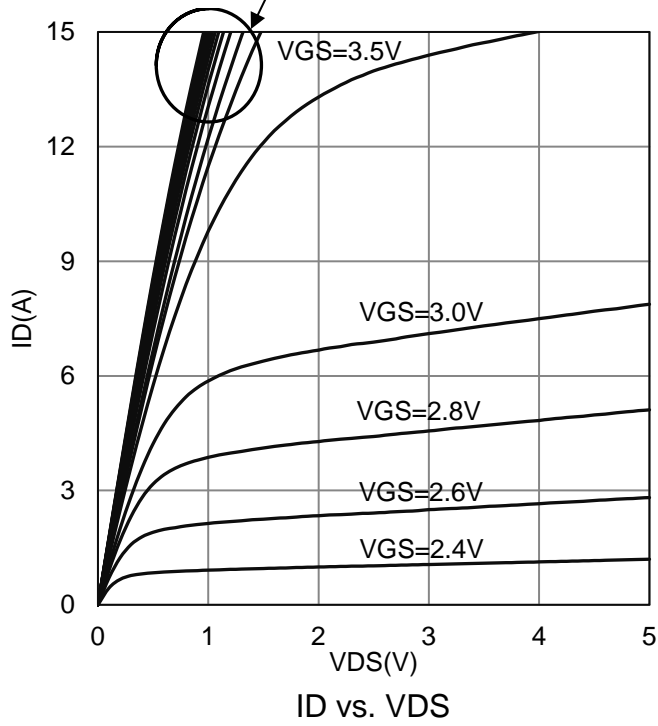
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit	
Static						
Drain–Source Breakdown Voltage (VGS = 0 V, ID = -250 μA)	VBRDSS	-60	-	-	V	
Gate Threshold Voltage (VDS = VGS, ID = -250 μA)	VGS(th)	-1	-	-2.5	V	
Gate Leakage Current (VDS = 0 V, VGS = ±20 V)	IGSS	-	-	±100	nA	
Zero Gate Voltage Drain Current (VDS = -48 V, VGS = 0 V)	IDSS	-	-	-1	μA	
Drain-Source On-Resistance(Note 3) (VGS = -10 V, ID = -3.6 A) (VGS = -4.5 V, ID = -2.5 A)	RDS(ON)	-	-	60 85	mΩ	
Diode Forward Voltage (IS = -1 A, VGS = 0 V)	VSD	-	-	-1.2	V	
Dynamic						
Total Gate Charge	(VDS= -30 V, VGS = -4.5 V, ID= -3.6 A)	Qg	-	9	-	nC
Gate-Source Charge		Qgs	-	2.9	-	
Gate-Drain Charge		Qgd	-	3.5	-	
Turn-On Delay Time	(VDS = -30 V, RL = 3 Ω, ID = -10 A, VGEN = -10 V, RGEN = 6 Ω)	td(on)	-	6.6	-	ns
Rise Time		tr	-	8	-	
Turn-Off Delay Time		td(off)	-	55	-	
Fall Time		tf	-	21	-	
Input Capacitance	(VDS = -30 V, VGS = 0 V, f = 1 MHz)	Ciss	-	1170	-	pF
Output Capacitance		Coss	-	61	-	
Reverse Transfer Capacitance		Crss	-	46	-	

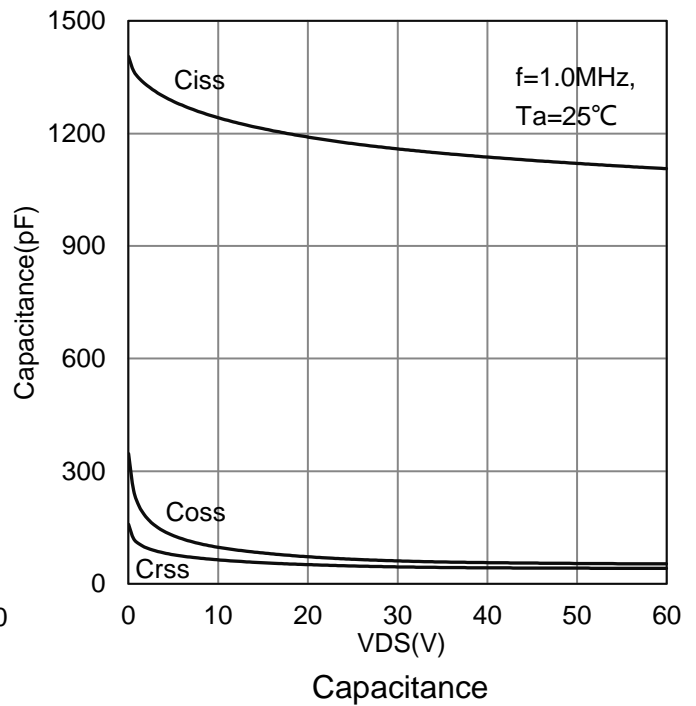
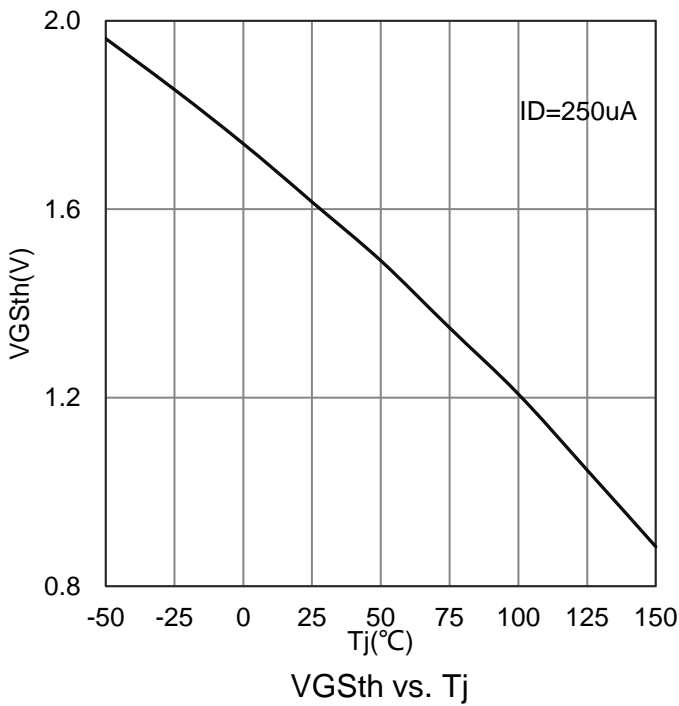
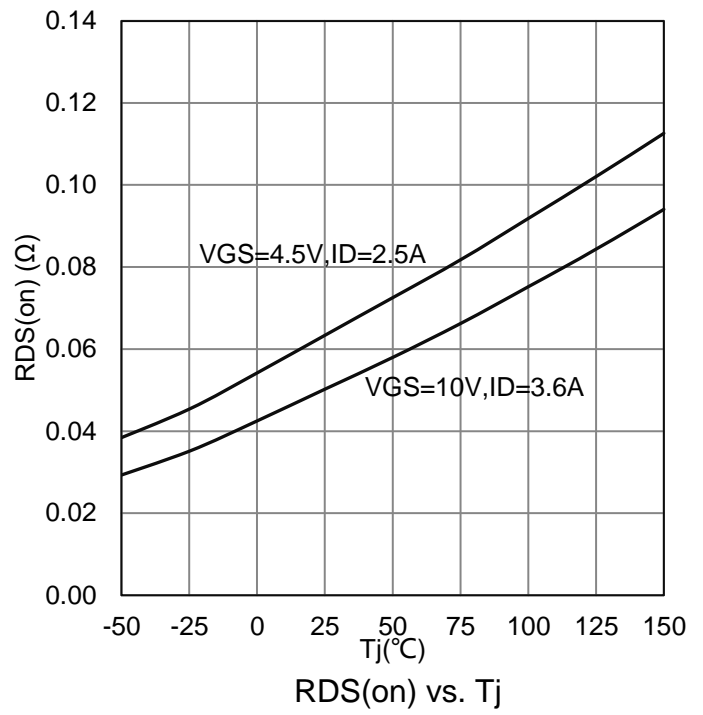
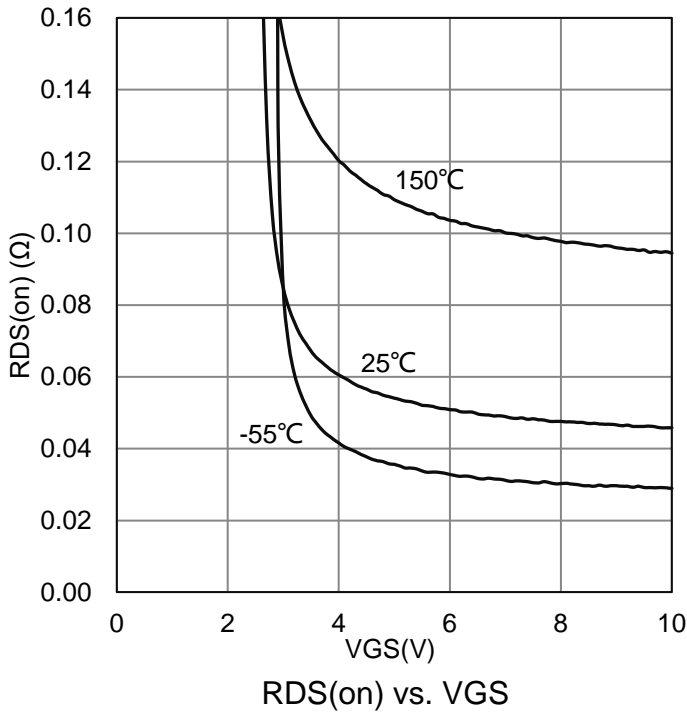
3. Pulse test: PW ≤ 300us duty cycle ≤ 2%.

7. ELECTRICAL CHARACTERISTICS CURVES

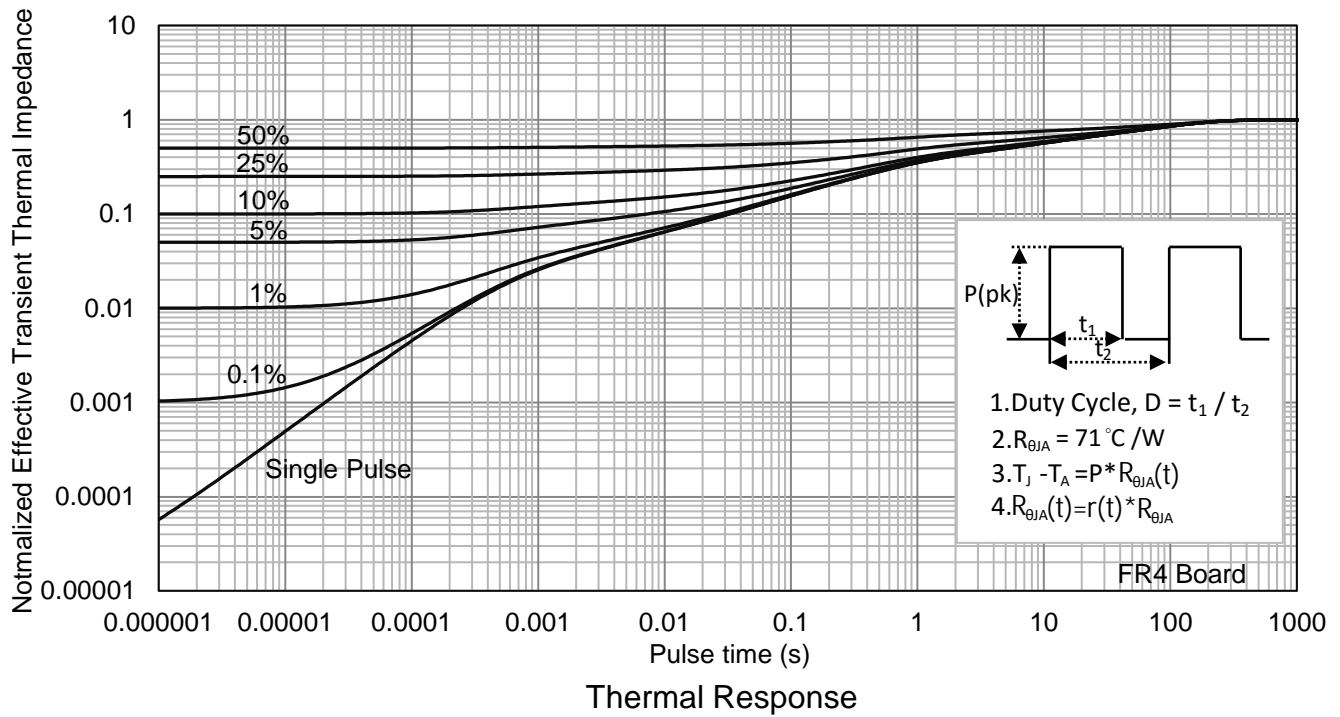
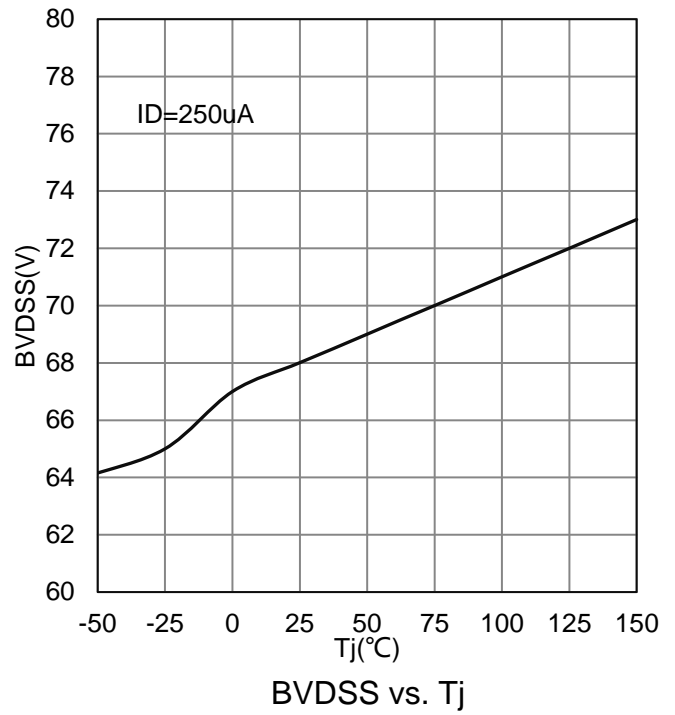
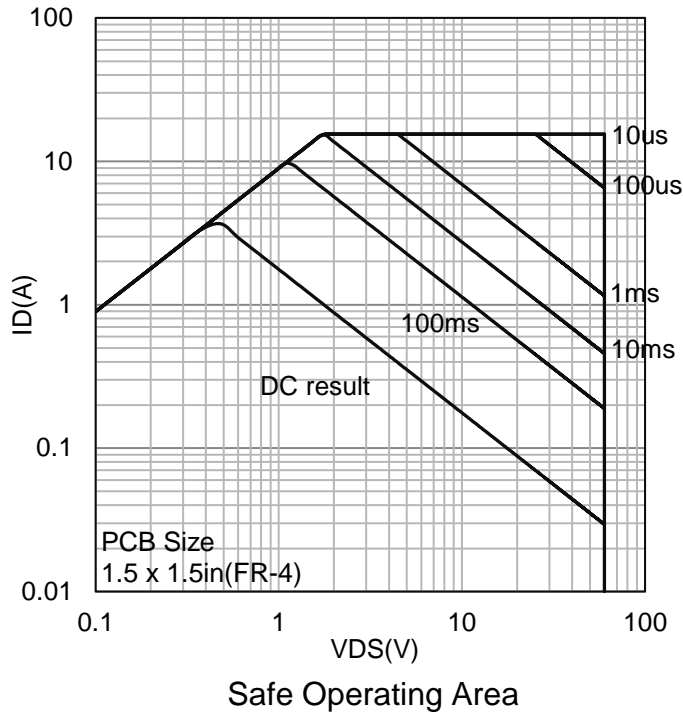
VGS=4V,4.5V,5V,5.5V,6V,6.5V,7V,7.5V,8V,8.5V,9V,9.5V,10V



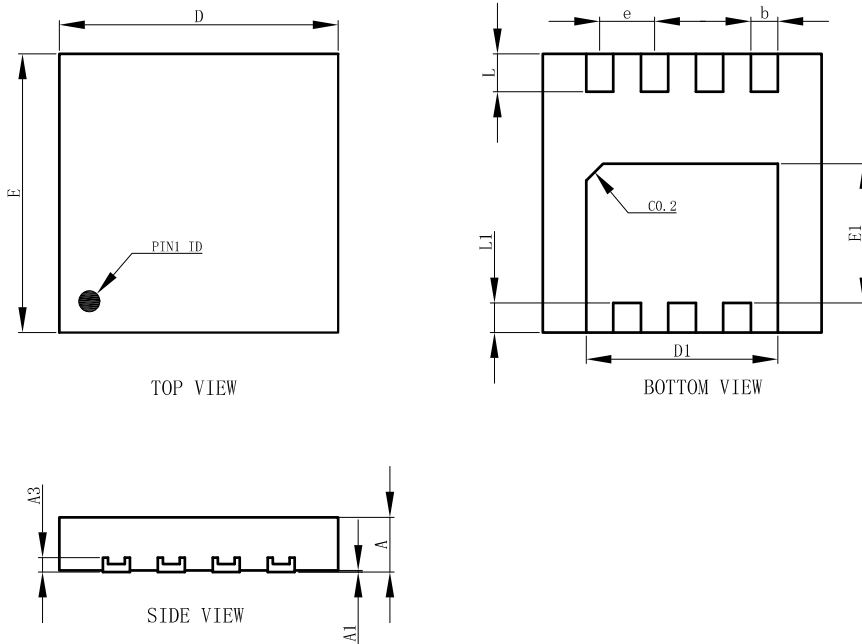
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

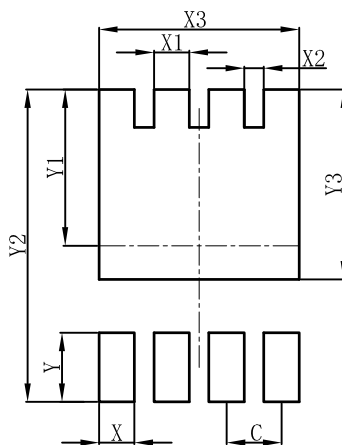


8. OUTLINE AND DIMENSIONS



DFN3333-8A			
DIM	MIN	NOR	MAX
A	0.60	0.65	0.70
A1	0.00	0.03	0.05
b	0.27	0.32	0.37
D	3.25	3.30	3.35
E	3.25	3.30	3.35
D1	2.22	2.27	2.32
E1	1.60	1.65	1.70
e	0.65BSC		
L	0.40	0.45	0.50
L1	0.30	0.35	0.40
A3	0.152REF.		
All Dimensions in mm			

9. SOLDERING FOOTPRINT



DFN3333-8A	
DIM	(mm)
C	0.65
X	0.42
X1	0.42
X2	0.23
X3	2.37
Y	0.70
Y1	1.85
Y2	3.70
Y3	2.25

DISCLAIMER

- Before you use our Products, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.
- The information contained in this document is provided on an "as is" basis and LRC does not warrant that all information contained in this document is accurate and/or error-free. LRC shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.